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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	109
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	132-UFBGA
Supplier Device Package	132-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476qei6

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3.7 Boot modes

At startup, BOOT0 pin and BOOT1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART, I2C, SPI, CAN and USB OTG FS in Device mode through DFU (device firmware upgrade).

3.8 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.9 Power supply management

3.9.1 Power supply schemes

- V_{DD} = 1.71 to 3.6 V: external power supply for I/Os (V_{DDIO1}), the internal regulator and the system analog such as reset, power management and internal clocks. It is provided externally through V_{DD} pins.
- V_{DDA} = 1.62 V (ADCs/COMPs) / 1.8 (DACs/OPAMPs) to 3.6 V: external analog power supply for ADCs, DACs, OPAMPs, Comparators and Voltage reference buffer. The V_{DDA} voltage level is independent from the V_{DD} voltage.
- V_{DDUSB} = 3.0 to 3.6 V: external independent power supply for USB transceivers. The V_{DDUSB} voltage level is independent from the V_{DD} voltage.
- V_{DDIO2} = 1.08 to 3.6 V: external power supply for 14 I/Os (PG[15:2]). The V_{DDIO2} voltage level is independent from the V_{DD} voltage.
- V_{LCD} = 2.5 to 3.6 V: the LCD controller can be powered either externally through VLCD pin, or internally from an internal voltage generated by the embedded step-up converter.
- V_{BAT} = 1.55 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Note: When the functions supplied by V_{DDA}, V_{DDUSB} or V_{DDIO2} are not used, these supplies should preferably be shorted to V_{DD}.

Note: If these supplies are tied to ground, the I/Os supplied by these power supplies are not 5 V tolerant (refer to Table 19: Voltage characteristics).

Note: V_{DDIOx} is the I/Os general purpose digital functions supply. V_{DDIOx} represents V_{DDIO1} or V_{DDIO2}, with V_{DDIO1} = V_{DD}. V_{DDIO2} supply voltage level is independent from V_{DDIO1}.

Table 4. STM32L476 modes overview (continued)

Mode	Regulator (1)	CPU	Flash	SRAM	Clocks	DMA & Peripherals(2)	Wakeup source	Consumption(3)	Wakeup time
Stop 1	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1,2) DACx (x=1,2) OPAMPx (x=1,2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1..2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) OTG_FS(8) SWPMI1(9)	6.6 µA w/o RTC 6.9 µA w RTC	4 µs in SRAM 6 µs in Flash
Stop 2	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1..2) I2C3(7) LPUART1(6) LPTIM1 *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1..2) I2C3(7) LPUART1(6) LPTIM1	1.1 µA w/o RTC 1.4 µA w/RTC	5 µs in SRAM 7 µs in Flash

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
59	A7	A7	93	B4	137	PB7	I/O	FT_fla	-	LPTIM1_IN2, TIM4_CH2, TIM8_BKIN, I2C1_SDA, DFSDM_CKIN5, USART1_RX, UART4_CTS, TSC_G2_IO4, LCD_SEG21, FMC_NL, TIM8_BKIN_COMP1, TIM17_CH1N, EVENTOUT	COMP2_INM, PVD_IN
60	D7	D7	94	A4	138	BOOT0	I	-	-	-	-
61	E7	E7	95	A3	139	PB8	I/O	FT_fl	-	TIM4_CH3, I2C1_SCL, DFSDM_DATIN6, CAN1_RX, LCD_SEG16, SDMMC1_D4, SAI1_MCLK_A, TIM16_CH1, EVENTOUT	-
62	E8	E8	96	B3	140	PB9	I/O	FT_fl	-	IR_OUT, TIM4_CH4, I2C1_SDA, SPI2_NSS, DFSDM_CKIN6, CAN1_TX, LCD_COM3, SDMMC1_D5, SAI1_FS_A, TIM17_CH1, EVENTOUT	-
-	-	-	97	C3	141	PE0	I/O	FT_l	-	TIM4_ETR, LCD_SEG36, FMC_NBL0, TIM16_CH1, EVENTOUT	-
-	-	-	98	A2	142	PE1	I/O	FT_l	-	LCD_SEG37, FMC_NBL1, TIM17_CH1, EVENTOUT	-
63	A8	A8	99	D3	143	VSS	S	-	-	-	-
64	A9	A9	100	C4	144	VDD	S	-	-	-	-

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF
   - These GPIOs must not be used as current sources (e.g. to drive an LED).

2. After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the RM0351 reference manual.

3. After reset, these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13, PB4 pins and the internal pull-down on PA14 pin are activated.

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see *Table 17*)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2/ TIM5/TIM8/ LPTIM1	TIM1/TIM2/ TIM3/TIM4/ TIM5	TIM8	I2C1/I2C2/I2C3	SPI1/SPI2	SPI3/DFSDM	USART1/ USART2/ USART3
Port A	PA0	-	TIM2_CH1	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS_ DE
	PA2	-	TIM2_CH3	TIM5_CH3	-	-	-	-	USART2_TX
	PA3	-	TIM2_CH4	TIM5_CH4	-	-	-	-	USART2_RX
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS	USART2_CK
	PA5	-	TIM2_CH1	TIM2_ETR	TIM8_CH1N	-	SPI1_SCK	-	-
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	USART3_CTS
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-
	PA8	MCO	TIM1_CH1	-	-	-	-	-	USART1_CK
	PA9	-	TIM1_CH2	-	-	-	-	-	USART1_TX
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX
	PA11	-	TIM1_CH4	TIM1_BKIN2	-	-	-	-	USART1_CTS
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS_ DE
	PA13	JTMS-SWDIO	IR_OUT	-	-	-	-	-	-
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-
	PA15	JTDI	TIM2_CH1	TIM2_ETR	-	-	SPI1_NSS	SPI3_NSS	-

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see *Table 16*) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port B	PB0	-	-	QUADSPI_BK1_IO1	LCD_SEG5	COMP1_OUT	-	-	EVENTOUT
	PB1	-	-	QUADSPI_BK1_IO0	LCD_SEG6	-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	-	-	-	-	-	EVENTOUT
	PB3	-	-	-	LCD_SEG7	-	SAI1_SCK_B	-	EVENTOUT
	PB4	UART5_RTS_DE	TSC_G2_IO1	-	LCD_SEG8	-	SAI1_MCLK_B	TIM17_BKIN	EVENTOUT
	PB5	UART5_CTS	TSC_G2_IO2	-	LCD_SEG9	COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	-	TSC_G2_IO3	-	-	TIM8_BKIN2_COMP2	SAI1_FS_B	TIM16_CH1N	EVENTOUT
	PB7	UART4_CTS	TSC_G2_IO4	-	LCD_SEG21	FMC_NL	TIM8_BKIN_COMP1	TIM17_CH1N	EVENTOUT
	PB8	-	CAN1_RX	-	LCD_SEG16	SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	-	CAN1_TX	-	LCD_COM3	SDMMC1_D5	SAI1_FS_A	TIM17_CH1	EVENTOUT
	PB10	LPUART1_RX	-	QUADSPI_CLK	LCD_SEG10	COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	QUADSPI_NCS	LCD_SEG11	COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RTS_DE	TSC_G1_IO1	-	LCD_SEG12	SWPMI1_IO	SAI2_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CTS	TSC_G1_IO2	-	LCD_SEG13	SWPMI1_TX	SAI2_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-	LCD_SEG14	SWPMI1_RX	SAI2_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-	LCD_SEG15	SWPMI1_SUSPEND	SAI2_SD_A	TIM15_CH2	EVENTOUT

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see *Table 16*) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port F	PF0	-	-	-	-	FMC_A0	-	-	EVENTOUT
	PF1	-	-	-	-	FMC_A1	-	-	EVENTOUT
	PF2	-	-	-	-	FMC_A2	-	-	EVENTOUT
	PF3	-	-	-	-	FMC_A3	-	-	EVENTOUT
	PF4	-	-	-	-	FMC_A4	-	-	EVENTOUT
	PF5	-	-	-	-	FMC_A5	-	-	EVENTOUT
	PF6	-	-	-	-	-	SAI1_SD_B	-	EVENTOUT
	PF7	-	-	-	-	-	SAI1_MCLK_B	-	EVENTOUT
	PF8	-	-	-	-	-	SAI1_SCK_B	-	EVENTOUT
	PF9	-	-	-	-	-	SAI1_FS_B	TIM15_CH1	EVENTOUT
	PF10	-	-	-	-	-	-	TIM15_CH2	EVENTOUT
	PF11	-	-	-	-	-	-	-	EVENTOUT
	PF12	-	-	-	-	FMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	FMC_A7	-	-	EVENTOUT
	PF14	-	TSC_G8_IO1	-	-	FMC_A8	-	-	EVENTOUT
	PF15	-	TSC_G8_IO2	-	-	FMC_A9	-	-	EVENTOUT

2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
5. Include VREF- pin.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
ΣIV_{DD}	Total current into sum of all V_{DD} power lines (source)(1)	150	mA
ΣIV_{SS}	Total current out of sum of all V_{SS} ground lines (sink)(1)	150	
$IV_{DD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$IV_{SS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin except FT_f	20	
	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(2)	100	
	Total output current sourced by sum of all I/Os and control pins(2)	100	
$I_{INJ(PIN)}$(3)	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0(4)	
	Injected current on PA4, PA5	-5/0	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/Os and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DDIOx}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer also to *Table 19: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 21. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 48 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 45*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 45. HSE oscillator characteristics(1)

Symbol	Parameter	Conditions(2)	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	48	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
$I_{DD(HSE)}$	HSE current consumption	During startup(3)	-	-	5.5	mA
		V_{DD} = 3 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.44	-	
		V_{DD} = 3 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.45	-	
		V_{DD} = 3 V, Rm = 30 Ω, CL = 5 pF@48 MHz	-	0.68	-	
		V_{DD} = 3 V, Rm = 30 Ω, CL = 10 pF@48 MHz	-	0.94	-	
		V_{DD} = 3 V, Rm = 30 Ω, CL = 20 pF@48 MHz	-	1.77	-	
G_m	Maximum critical crystal transconductance	Startup	-	-	1.5	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 18*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Figure 20. HSI16 frequency versus temperature

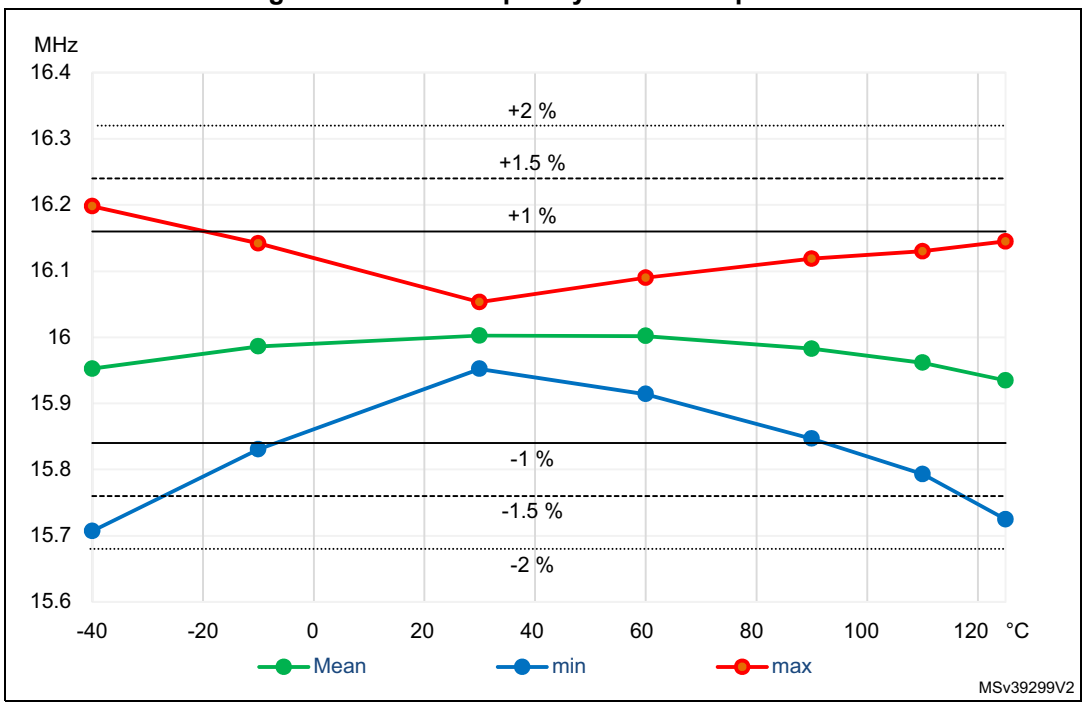
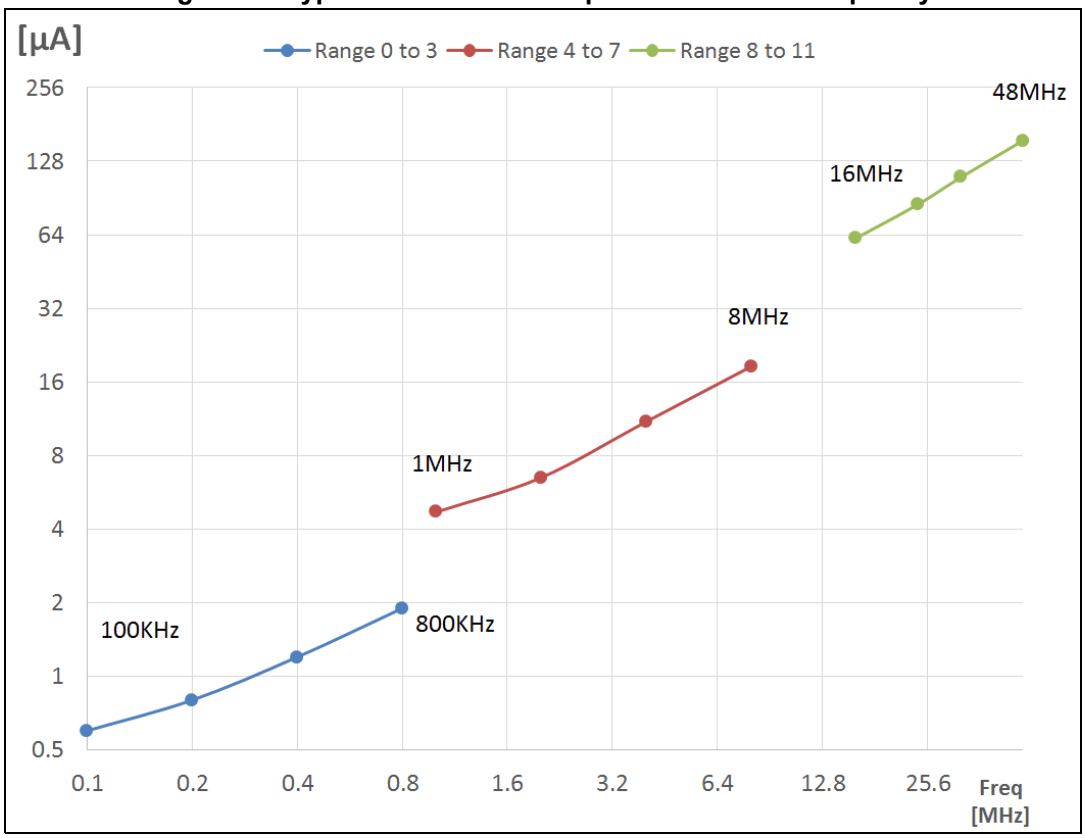


Table 48. MSI oscillator characteristics(1) (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit
Δ_{VDD}(MSI)(2)	MSI oscillator frequency drift over V_{DD} (reference is 3 V)	MSI mode	Range 0 to 3	V_{DD}=1.62 V to 3.6 V	-1.2	-	0.5	%
				V_{DD}=2.4 V to 3.6 V	-0.5	-		
			Range 4 to 7	V_{DD}=1.62 V to 3.6 V	-2.5	-	0.7	
				V_{DD}=2.4 V to 3.6 V	-0.8	-		
			Range 8 to 11	V_{DD}=1.62 V to 3.6 V	-5	-	1	
				V_{DD}=2.4 V to 3.6 V	-1.6	-		
$\Delta F_{SAMPLING}$ (MSI)(2)(6)	Frequency variation in sampling mode(3)	MSI mode	T_A= -40 to 85 °C		-	1	2	%
			T_A= -40 to 125 °C		-	2	4	
P_USB Jitter(MSI)(6)	Period jitter for USB clock(4)	PLL mode Range 11	for next transition	-	-	-	3.458	ns
			for paired transition	-	-	-	3.916	
MT_USB Jitter(MSI)(6)	Medium term jitter for USB clock(5)	PLL mode Range 11	for next transition	-	-	-	2	ns
			for paired transition	-	-	-	1	
CC jitter(MSI)(6)	RMS cycle-to-cycle jitter	PLL mode Range 11		-	-	60	-	ps
P jitter(MSI)(6)	RMS Period jitter	PLL mode Range 11		-	-	50	-	ps
t_{SU}(MSI)(6)	MSI oscillator start-up time	Range 0		-	-	10	20	us
		Range 1		-	-	5	10	
		Range 2		-	-	4	8	
		Range 3		-	-	3	7	
		Range 4 to 7		-	-	3	6	
		Range 8 to 11		-	-	2.5	6	
t_{STAB}(MSI)(6)	MSI oscillator stabilization time	PLL mode Range 11	10 % of final frequency	-	-	0.25	0.5	ms
			5 % of final frequency	-	-	0.5	1.25	
			1 % of final frequency	-	-	-	2.5	

Figure 21. Typical current consumption versus MSI frequency



Low-speed internal (LSI) RC oscillator

Table 49. LSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSI}	LSI Frequency	V_{DD} = 3.0 V, T_A = 30 °C	31.04	-	32.96	kHz
		V_{DD} = 1.62 to 3.6 V, TA = -40 to 125 °C	29.5	-	34	
$t_{SU}(LSI)^{(2)}$	LSI oscillator start-up time	-	-	80	130	µs
$t_{STAB}(LSI)^{(2)}$	LSI oscillator stabilisation time	5% of final frequency	-	125	180	µs
$I_{DD}(LSI)^{(2)}$	LSI oscillator power consomption	-	-	110	180	nA

1. Guaranteed by characterization results.
2. Guaranteed by design.

6.3.9 PLL characteristics

The parameters given in *Table 50* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 53*. They are based on the EMS levels and classes defined in application note AN1709.

Table 53. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 80 MHz, conforming to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 80 MHz, conforming to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

1. Guaranteed by design, unless otherwise specified.
2. Refer to *Table 25: Embedded internal voltage reference*.
3. Guaranteed by characterization results.

6.3.21 Operational amplifiers characteristics

Table 73. OPAMP characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage(2)	-		1.8	-	3.6	V
CMIR	Common mode input range	-		0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	25 °C, No Load on output.		-	-	±1.5	mV
		All voltage/Temp.		-	-	±3	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode		-	±5	-	µV/°C
		Low-power mode		-	±10	-	
TRIMOFFSETP TRIMLPOFFSETP	Offset trim step at low common input voltage (0.1 x V_{DDA})	-		-	0.8	1.1	mV
TRIMOFFSETN TRIMLPOFFSETN	Offset trim step at high common input voltage (0.9 x V_{DDA})	-		-	1	1.35	
I_{LOAD}	Drive current	Normal mode	$V_{DDA} \geq 2$ V	-	-	500	µA
		Low-power mode		-	-	100	
I_{LOAD_PGA}	Drive current in PGA mode	Normal mode	$V_{DDA} \geq 2$ V	-	-	450	
		Low-power mode		-	-	50	
R_{LOAD}	Resistive load (connected to VSSA or to VDDA)	Normal mode	$V_{DDA} < 2$ V	4	-	-	kΩ
		Low-power mode		20	-	-	
R_{LOAD_PGA}	Resistive load in PGA mode (connected to VSSA or to V_{DDA})	Normal mode	$V_{DDA} < 2$ V	4.5	-	-	
		Low-power mode		40	-	-	
C_{LOAD}	Capacitive load	-		-	-	50	pF
CMRR	Common mode rejection ratio	Normal mode		-	-85	-	dB
		Low-power mode		-	-90	-	

6.3.25 DFSDM characteristics

Unless otherwise specified, the parameters given in *Table 78* for DFSDM are derived from tests performed under the ambient temperature, f_{APB2} frequency and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*.

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x VDD

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (DFSDM_CKINy, DFSDM_DATINy, DFSDM_CKOUT for DFSDM).

Table 78. DFSDM characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	-	-	-	f_{SYSCLK}	MHz
f_{CKIN} ($1/T_{CKIN}$)	Input clock frequency	SPI mode (SITP[1:0] = 01)	-	-	20 ($f_{DFSDMCLK}$/4)	
f_{CKOUT}	Output clock frequency	-	-	-	20	MHz
$DuCy_{CKOUT}$	Output clock frequency duty cycle	-	45	50	55	%
$t_{wh(CKIN)}$ $t_{wl(CKIN)}$	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0)	T_{CKIN}/2-0.5	T_{CKIN}/2	-	ns
t_{su}	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	0	-	-	
t_h	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	2	-	-	
$T_{Manchester}$	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] ≠ 0)	(CKOUT DIV+1) x $T_{DFSDMCLK}$	-	(2 x CKOUTDIV) x $T_{DFSDMCLK}$	

1. Data based on characterization results, not tested in production.

Table 79. TIMx(1) characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 80 MHz	12.5	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 80 MHz	0	40	MHz
Res_{TIM}	Timer resolution	TIMx (except TIM2 and TIM5)	-	16	bit
		TIM2 and TIM5	-	32	
$t_{COUNTER}$	16-bit counter clock period	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 80 MHz	0.0125	819.2	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 80 MHz	-	53.68	s

1. TIMx is used as a general term in which x stands for 1,2,3,4,5,6,7,8,15,16 or 17.

Table 80. IWDG min/max timeout period at 32 kHz (LSI)(1)

Prescaler divider	PR[2:0] bits	Min timeout RL[11:0]= 0x000	Max timeout RL[11:0]= 0xFFF	Unit
/4	0	0.125	512	ms
/8	1	0.250	1024	
/16	2	0.500	2048	
/32	3	1.0	4096	
/64	4	2.0	8192	
/128	5	4.0	16384	
/256	6 or 7	8.0	32768	

1. The exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 81. WWDG min/max timeout value at 80 MHz (PCLK)

Prescaler	WDGTB	Min timeout value	Max timeout value	Unit
1	0	0.0512	3.2768	ms
2	1	0.1024	6.5536	
4	2	0.2048	13.1072	
8	3	0.4096	26.2144	

SAI characteristics

Unless otherwise specified, the parameters given in *Table 86* for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 86. SAI characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	SAI Main clock output	-	-	50	MHz
f_{CK}	SAI clock frequency(2)	Master transmitter $2.7 \le V_{DD} \le 3.6$ Voltage Range 1	-	18.5	MHz
		Master transmitter $1.71 \le V_{DD} \le 3.6$ Voltage Range 1	-	12.5	
		Master receiver Voltage Range 1	-	25	
		Slave transmitter $2.7 \le V_{DD} \le 3.6$ Voltage Range 1	-	22.5	
		Slave transmitter $1.71 \le V_{DD} \le 3.6$ Voltage Range 1	-	14.5	
		Slave receiver Voltage Range 1	-	25	
		Voltage Range 2	-	12.5	
$t_{v(FS)}$	FS valid time	Master mode $2.7 \le V_{DD} \le 3.6$	-	22	ns
		Master mode $1.71 \le V_{DD} \le 3.6$	-	40	
$t_{h(FS)}$	FS hold time	Master mode	10	-	ns
$t_{su(FS)}$	FS setup time	Slave mode	1	-	ns
$t_{h(FS)}$	FS hold time	Slave mode	2	-	ns
$t_{su(SD\_A\_MR)}$	Data input setup time	Master receiver	2.5	-	ns
$t_{su(SD\_B\_SR)}$		Slave receiver	3	-	
$t_{h(SD\_A\_MR)}$	Data input hold time	Master receiver	8	-	ns
$t_{h(SD\_B\_SR)}$		Slave receiver	4	-	

Figure 38. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

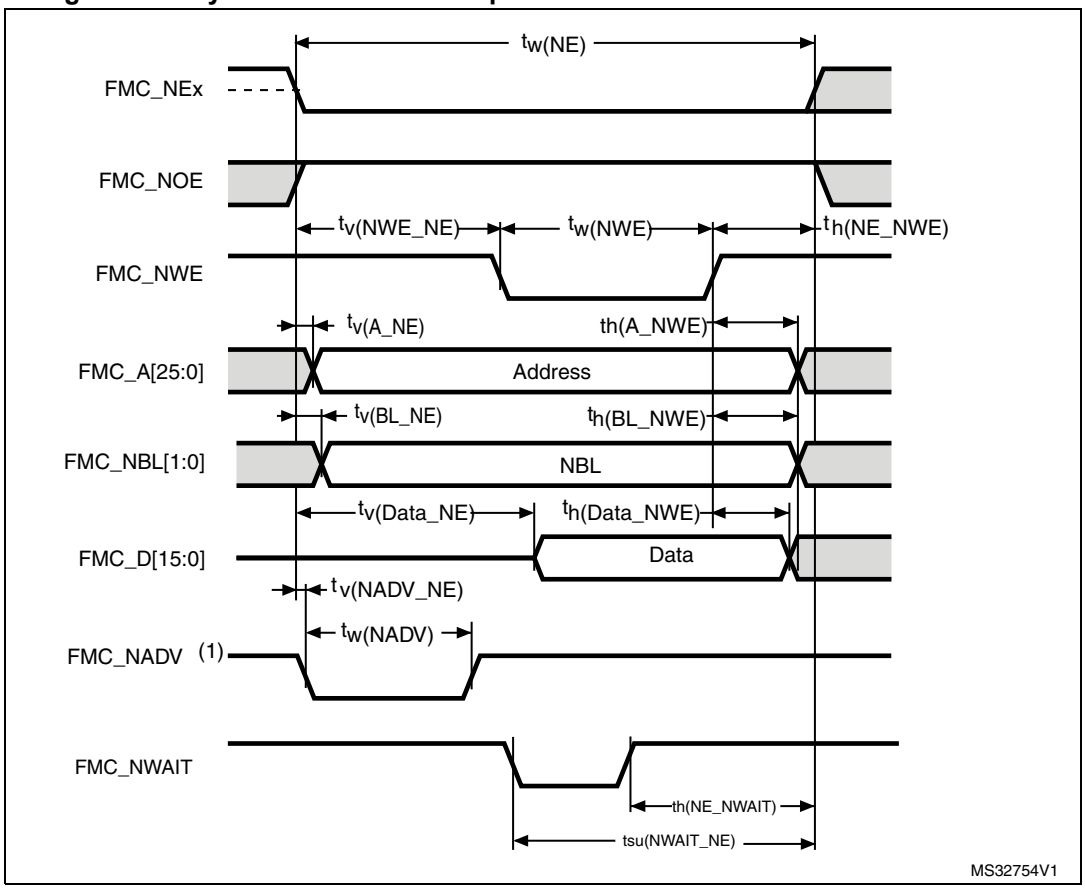


Table 92. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$-1	$3T_{HCLK}$+2	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	T_{HCLK}-0.5	T_{HCLK}+1.5	
$t_{w(NWE)}$	FMC_NWE low time	T_{HCLK}-1	T_{HCLK}+1	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}-0.5	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}-1	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	1.5	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	T_{HCLK}-0.5	-	
$t_{v(Data\_NE)}$	Data to FMC_NEx low to Data valid	-	T_{HCLK}+4	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	T_{HCLK}+1	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	1	
$t_{w(NADV)}$	FMC_NADV low time	-	T_{HCLK}+0.5	

1. CL = 30 pF.
2. Guaranteed by characterization results.

Figure 43. Synchronous non-multiplexed NOR/PSRAM read timings

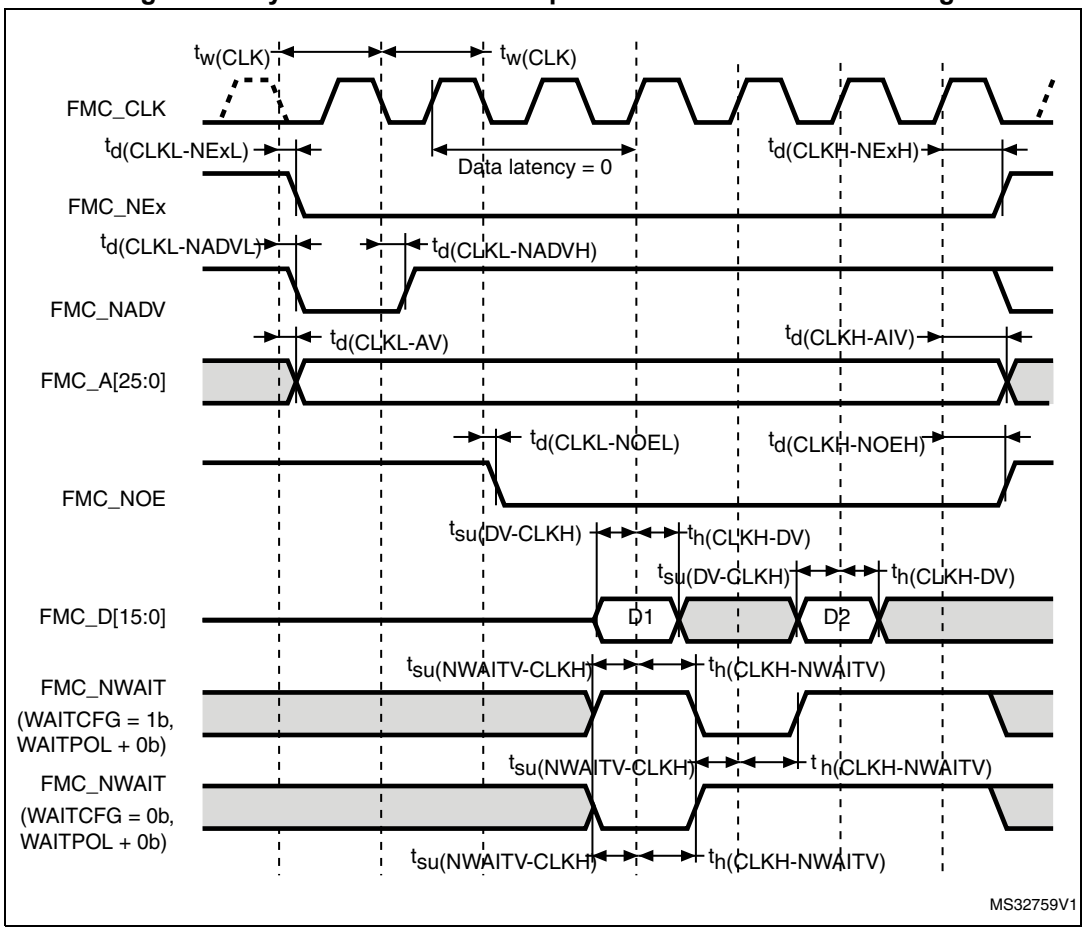


Table 100. Synchronous non-multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2.5	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	T_{HCLK}-0.5	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	2	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0.5	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	3.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	2	
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	T_{HCLK}-0.5	-	
$t_{su(DV-CLKH)}$	FMC_D[15:0] valid data before FMC_CLK high	0	-	
$t_{h(CLKH-DV)}$	FMC_D[15:0] valid data after FMC_CLK high	5	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	0	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	4	-	